

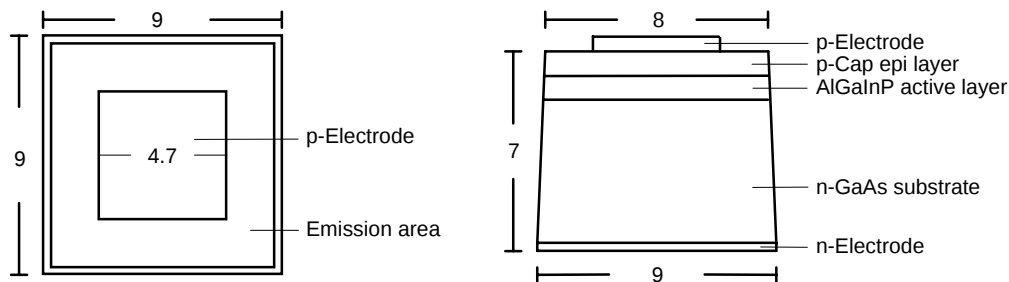
■ Features :

- MOVPE epi wafer
- Suitable for new creative products

■ Typical Applications :

- SMD Chip LED
- Display

■ Outline Dimensions : (Unit: mil)



■ Physical Structure :

Chip dimension	Chip size	9.0 mils x 9.0 mils
	Thickness	7.0 mils
	Emission area	8.0 mils
	Bonding pad	4.7 mils
Electrode	Top: P (anode)	Aluminum (Gold optional)
	Backside: N (cathode)	Gold alloy
Surface condition	Not frosted	

■ Electro-Optical Characteristics : (Ta = 25°C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	V_F	$I_F = 20 \text{ mA}$	-	1.95	2.40	V
Reverse Voltage	V_R	$I_R = 10 \mu\text{A}$	5	-	-	V
Wavelength	λ_D	$I_F = 20 \text{ mA}$	-	624	-	nm
	Hue		611	621	631	
Spectral width at half height	$\Delta\lambda$	$I_F = 20 \text{ mA}$	-	20	-	nm
Luminous Intensity	I_v	$I_F = 20 \text{ mA}$	D	40	-	mcd
			E	60	-	
			F	70	-	
			G	80	-	

■ Typical Electro-Optical Characteristics Curve:

Fig 1. Forward Current vs. Forward Voltage

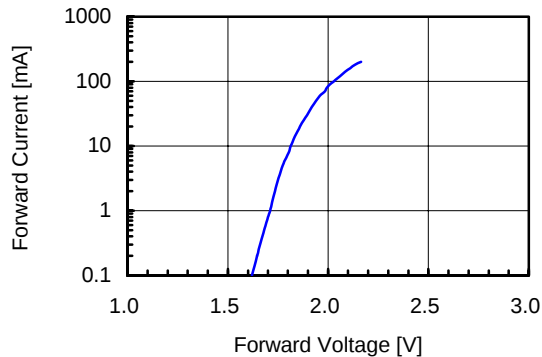


Fig 2. Relative Intensity vs. Forward Current

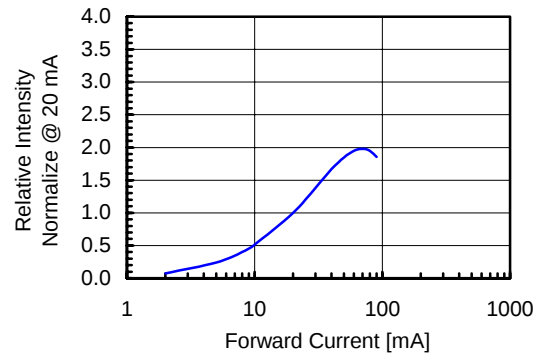


Fig 3. Forward Voltage vs. Temperature

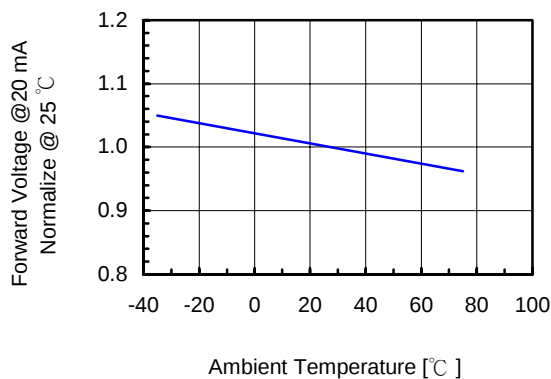


Fig 4. Relative Intensity vs. Temperature

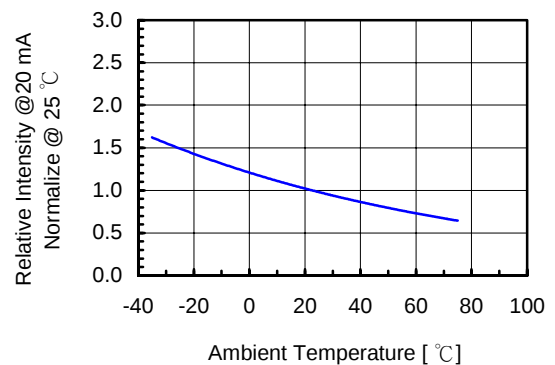
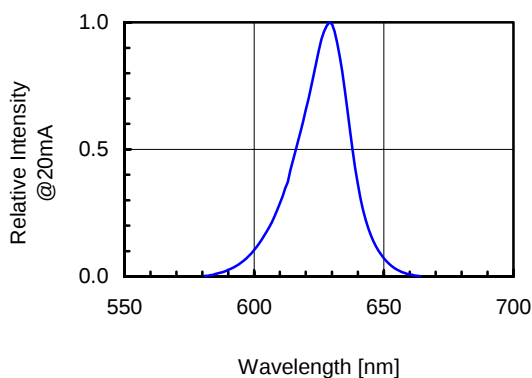


Fig 5. Relative Intensity vs. Wavelength



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